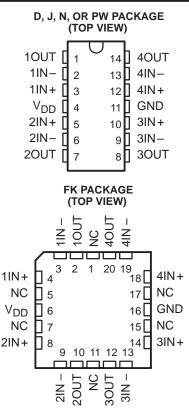
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- Trimmed Offset Voltage: TLC27M9 . . . 900 μ V Max at T_A = 25°C, V_{DD} = 5 V
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over Specified Temperature Range: 0°C to 70°C ... 3 V to 16 V -40°C to 85°C ... 4 V to 16 V -55°C to 125°C ... 4 V to 16 V
- Single-Supply Operation
- Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix, I-Suffix Types)
- Low Noise . . . Typically 32 nV/\/Hz at f = 1 kHz
- Low Power . . . Typically 2.1 mW at T_A = 25°C, V_{DD} = 5 V
- Output Voltage Range Includes Negative Rail
- High Input Impedance . . . $10^{12} \Omega$ Typ
- ESD-Protection Circuitry
- Small-Outline Package Option Also Available in Tape and Reel
- Designed-In Latch-Up Immunity

description

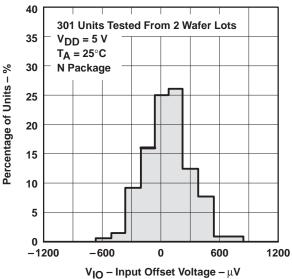
The TLC27M4 and TLC27M9 quad operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, low noise, and speeds comparable to that of general-purpose bipolar devices. These devices use Texas Instruments silicon-gate LinCMOS[™] technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, make these cost-effective devices ideal for applications that have previously been reserved for general-purpose bipolar products, but with only a fraction of the power consumption.



NC - No internal connection







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description (continued)

Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27M4 (10 mV) to the high-precision TLC27M9 (900 μ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

In general, many features associated with bipolar technology are available on LinCMOS[™] operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27M4 and TLC27M9. The devices also exhibit low voltage single-supply operation, and low power consumption, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up.

The TLC27M4 and TLC27M9 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015; however, care should be exercised in handling these devices, as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of -55°C to 125°C.

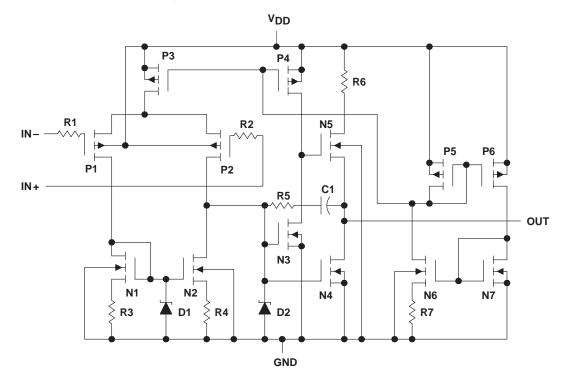
			-	PACKAGE			CLUID
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	CHIP FORM (Y)
	900 μV	TLC27M9CD	—	—	TLC27M9CN	—	—
0°C to 70°C	2 mV	TLC27M4BCD	—	—	TLC27M4BCN	—	—
0010700	5 mV	TLC27M4ACD	—	—	TLC27M4ACN	—	—
	10 mV	TLC27M4CD	—	—	TLC27M4CN	TLC27M4CPW	TLC27M4Y
	900 μV	TLC27M9ID	_	—	TLC27M9IN	_	—
-40°C to 85°C	2 mV	TLC27M4BID	_	—	TLC27M4BIN	—	—
-40 C 10 85 C	5 mV	TLC27M4AID	—	—	TLC27M4AIN	—	—
	10 mV	TLC27M4ID	—	—	TLC27M4IN	TLC27M41PW	—
-55°C to 125°C	900 μV	TLC27M9MD	TLC27M9MFK	TLC27M9MJ	TLC27M9MN	_	—
-55 C 10 125 C	10 mV	TLC27M4MD	TLC27M4MFK	TLC27M4MJ	TLC27M4MN	—	—

AVAILABLE OPTIONS

The D and PW package is available taped and reeled. Add R suffix to the device type (e.g., TLC279CDR).



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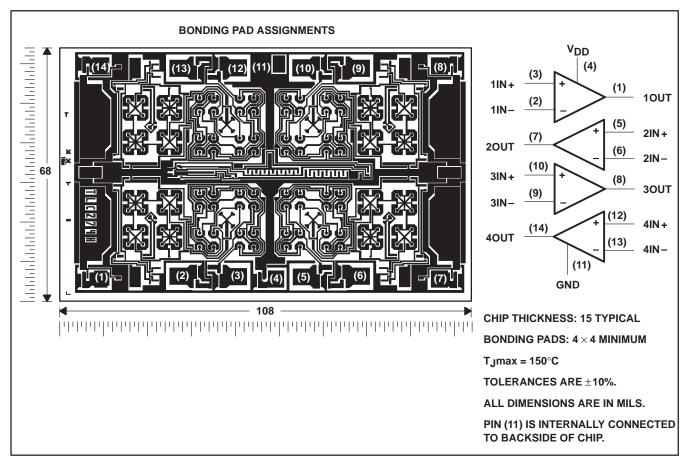
equivalent schematic (each amplifier)



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TLC27M4Y chip information

This chip, when properly assembled, displays characteristics similar to the TLC27M4C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{DD} (see Note 1)	
Input voltage range, V _I (any input)	
Output current, I _O (each output)±30 mA Total current into V _{DD}	
Total current out of GND	
Duration of short-circuit current at (or below) 25°C (see Note 3)	
Continuous total dissipation	
Operating free-air temperature, T _A : C suffix	
I suffix	
M suffix	
Storage temperature range65°C to 150°C	
Case temperature for 60 seconds: FK package 260°C	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, N, or PW package 260°C	
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: J package 300°C	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.

2. Differential voltages are at IN+ with respect to IN-.

3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	_
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
N	1575 mW	12.6 mW/°C	1008 mW	819 mW	_
PW	700 mW	5.6 mW/°C	448 mW	—	_

recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SU	FFIX	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, VDD		3	16	4	16	4	16	V
	$V_{DD} = 5 V$	-0.2	3.5	-0.2	3.5	0	3.5	V
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	v
Operating free-air temperature, T_A		0	70	-40	85	-55	125	°C



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAT		.C27M4 .C27M4 .C27M4 .C27M4 .C27M9	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27M4C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLC27M4C	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			12	
		TLC27M4AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
Vie	Input offset voltage	TLC27WI4AC	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	
VIO	input onset voltage	TLC274BC	V _O = 1.4 V,	VIC = 0,	25°C		250	2000	
		1627480	R _S = 50 Ω,	RL = 100 kΩ	Full range			3000	μV
		TLC279C	V _O = 1.4 V,	V _{IC} = 0,	25°C		210	900	μv
		1202750	R _S = 50 Ω,	R _L = 100 kΩ	Full range			1500	
ανιο	Average temperature coef	icient of input			25°C to 70°C		1.7		μV/°C
l. e	Input offect ourrept (coo N	ata (I)		V _{IC} = 2.5 V	25°C		0.1		۳Å
IIO	Input offset current (see N	Jle 4)	V _O = 2.5 V,	VIC = 2.5 V	70°C		7	300	pА
4	Input higg ourrant (ago Not	·•• 4)			25°C		0.6		۳Å
IВ	Input bias current (see Not	e 4)	V _O = 2.5 V,	V _{IC} = 2.5 V	70°C		40	600	pА
	Common-mode input volta	ao rongo			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	gerange			Full range	-0.2 to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	0°C	3	3.9		V
					70°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOT = 0	0°C		0	50	mV
					70°C		0	50	
	I am a final life of t				25°C	25	170		
AVD	Large-signal differential voltage amplification		$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 100 \text{ k}\Omega$	0°C	15	200		V/mV
					70°C	15	140		
					25°C	65	91		
CMRR	Common-mode rejection ra	atio	$V_{IC} = V_{ICR}min$		0°C	60	91		dB
					70°C	60	92		
		tio			25°C	70	93		
^k SVR	Supply-voltage rejection ra $(\Delta V_{DD}/\Delta V_{IO})$		$V_{DD} = 5 V \text{ to } 10 V,$	$V_{O} = 1.4 V$	0°C	60	92		dB
					70°C	60	94		
				$\lambda = 25\lambda$	25°C		420	1120	
IDD	Supply current (four amplif	iers)	$V_{O} = 2.5 V$, No load	$V_{IC} = 2.5 V,$	0°C		500	1280	μA
					70°C		340	880	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAţ		.C27M4 .C27M4 .C27M4 .C27M4	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27M4C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1602710140	R _S = 50 Ω,	RL = 100 kΩ	Full range			12	mV
		TLC27M4AC	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		0.9	5	IIIV
VIO	Input offset voltage		R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	
٩O	mput onset voltage	TLC27M4BC	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		260	2000	
			R _S = 50 Ω,	RL = 100 kΩ	Full range			3000	μV
		TLC27M9C	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		220	1200	μν
			R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			1900	
αΛΙΟ	Average temperature co- offset voltage	efficient of input			25°C to 70°C		2.1		μV/°C
l. e	Input offect ourrest (coo	Noto (1)		$\lambda = 5 \lambda$	25°C		0.1		۳Å
IO	Input offset current (see	Note 4)	V _O = 5 V,	$V_{IC} = 5 V$	70°C		7	300	pА
	Input high ourrest (see)	loto ()			25°C		0.7		~^
IВ	Input bias current (see N	lole 4)	V _O = 5 V,	$V_{IC} = 5 V$	70°C		50	600	pА
					25°C	-0.2 to	-0.3 to		V
Vion	Common-mode input vol	tage range				9	9.2		
VICR	(see Note 5)				Full range	-0.2 to 8.5			V
	· · · · · · · · · · · · · · · · · · ·				25°C	8	8.7		
Vон	High-level output voltage	•	V _{ID} = 100 mV,	RL = 100 kΩ	0°C	7.8	8.7		V
011	0 1 0			-	70°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	25	275		
Avd	Large-signal differential voltage amplification		$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 100 \text{ k}\Omega$	0°C	15	320		V/mV
	voltage amplification				70°C	15	230		
					25°C	65	94		
CMRR	Common-mode rejection	ratio	$V_{IC} = V_{ICR}min$		0°C	60	94		dB
					70°C	60	94		
					25°C	70	93		
ksvr	Supply-voltage rejection $(\Delta V_{DD}/\Delta V_{IO})$	ratio	$V_{DD} = 5 V$ to 10 V,	V _O = 1.4 V	0°C	60	92		dB
					70°C	60	94		
					25°C		570	1200	
IDD	Supply current (four amp	lifiers)	$V_{O} = 5 V$, No load	$V_{IC} = 5 V,$	0°C		690	1600	μA
					70°C		440	1120	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAţ	TL TL	.C27M4 .C27M4 .C27M4 .C27M4	AI BI	UNIT
						MIN	TYP	MAX	
		TLC27M4I	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		1.1	10	
		1 LC27 10141	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M4AI	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	IIIV
VIO	Input offset voltage		R _S = 50 Ω,	RL = 100 kΩ	Full range			6.5	
٩O	mput onset voltage	TLC27M4BI	V _O = 1.4 V,	VIC = 0,	25°C		250	2000	
			R _S = 50 Ω,	RL = 100 kΩ	Full range			3000	μV
		TLC27M9I	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		210	900	μν
			R _S = 50 Ω,	R _L = 100 kΩ	Full range			2000	
αΛΙΟ	Average temperature coef	ficient of input			25°C to 85°C		1.7		μV/°C
l. a	Input offset current (see N	oto (1)			25°C		0.1		۳Å
IO	input onset current (see N	ole 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	85°C		24	1000	pА
lun.	Input bias current (see Not			VIC = 2.5 V	25°C		0.6		۳Å
IВ	input bias current (see No	le 4)	V _O = 2.5 V,	VIC = 2.5 V	85°C		200	2000	pА
						-0.2	-0.3		
					25°C	to 4	to 4.2		V
VICR	Common-mode input volta (see Note 5)	ge range			Full range	-0.2 to	7.2		V
					0500	3.5	2.0		
Maria	Lligh lovel output voltogo		\/ 100 m\/	D. 100 kO	25°C -40°C	3.2 3	3.9 3.9		v
Vон	High-level output voltage		V _{ID} = 100 mV,	RL = 100 kΩ	=40°C 85°C	3	3.9		V
					25°C	3	4	50	
Val			V _{ID} = -100 mV,		-40°C		0	50	mV
VOL	Low-level output voltage		$v_{\rm ID} = -100 \mathrm{mv},$	IOT = 0	_40 C 85°C		0	50	mv
					25°C	25	170	50	
A _{VD}	Large-signal differential		$V_{O} = 0.25 \text{ V to 2 V},$	$R_{\rm L} = 100 \rm kO$	-40°C	15	270		V/mV
, , v D	voltage amplification			···L = 100 (/22	_40 C 85°C	15	130		v/111V
					25°C	65	91		
CMRR	Common-mode rejection ra	atio	VIC = VICRmin		-40°C	60	90		dB
2					40°C	60	90		
			1		25°C	70	93		
k SVR	Supply-voltage rejection ra	ntio	$V_{DD} = 5 V \text{ to } 10 V,$	Vo = 1.4 V	-40°C	60	91		dB
OVIX	$(\Delta V_{DD} / \Delta V_{IO})$			0	85°C	60	94		
			1		25°C		420	1120	
IDD	Supply current (four amplif	ïers)	V _O = 2.5 V,	$V_{IC} = 2.5 V_{,}$	-40°C		630	1600	μA
50	11 Y	- /	No load	чы – 2.0 v,	85°C		320	800	1

[†] Full range is -40° C to 85° C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAţ		.C27M4 .C27M4 .C27M4 .C27M4	AI BI	UNIT
						MIN	TYP	MAX	
		TLC27M4I	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1 LG27 10141	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M4AI	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		0.9	5	111 V
VIO	Input offset voltage		R _S = 50 Ω,	RL = 100 kΩ	Full range			7	
٩O	input onset voltage	TLC27M4BI	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		260	2000	
			R _S = 50 Ω,	RL = 100 kΩ	Full range			3500	μV
		TLC27M9I	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		220	1200	μν
		TEOZINIO	R _S = 50 Ω,	RL = 100 kΩ	Full range			2900	
αΛΙΟ	Average temperature coeff offset voltage	icient of input			25°C to 85°C		2.1		μV/°C
l. e	Input offect ourrept (coo N	(1)			25°C		0.1		۳Å
10	Input offset current (see No	ne 4)	V _O = 5 V,	$V_{IC} = 5 V$	85°C		26	1000	pА
	Input high ourrest (and Not	a 4)			25°C		0.7		~^
IВ	Input bias current (see Not	e 4)	V _O = 5 V,	$V_{IC} = 5 V$	85°C		220	2000	pА
	Common-mode input				25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	voltage range (see Note 5)				Full range	-0.2 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	-40°C	7.8	8.7		V
					85°C	7.8	8.7		
					25°C		0	50	
Vol	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	25	275		
AVD	Large-signal differential voltage amplification		$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 100 \text{ k}\Omega$	-40°C	15	390		V/mV
	vonago ampinioation				85°C	15	220		
					25°C	65	94		
CMRR	Common-mode rejection ra	atio	$V_{IC} = V_{ICR}min$		-40°C	60	93		dB
					85°C	60	94		
					25°C	70	93		
ksvr	Supply-voltage rejection ra $(\Delta V_{DD}/\Delta V_{IO})$	10	$V_{DD} = 5 V \text{ to } 10 V,$	$V_{O} = 1.4 V$	-40°C	60	91		dB
					85°C	60	94		
					25°C		570	1200	
IDD	Supply current (four amplif	iers)	$V_{O} = 5 V$, No load	$V_{IC} = 5 V,$	-40°C		900	1800	μΑ
					85°C		410	1040	

[†] Full range is -40° C to 85° C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	т _А †		C27M4N C27M9N		UNIT
						MIN	TYP	MAX	
		TLC27M4M	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		1.1	10	mV
VIO	Input offset voltage		R _S = 50 Ω,	RL = 100 kΩ	Full range			12	IIIV
۷IO	input onset voltage	TLC27M9M	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		210	900	μV
			R _S = 50 Ω,	RL = 100 kΩ	Full range			3750	μv
αΛΙΟ	Average temperature coefficie offset voltage	ent of input			25°C to 125°C		1.7		μV/°C
li o	Input offset current (see Note	4)	V _O = 2.5 V,	VIC = 2.5 V	25°C		0.1		pА
10	Input onset current (see Note	4)	VO = 2.5 V,	VIC = 2.5 V	125°C		1.4	15	nA
lin.	Input bias current (see Note 4	1	Vo - 25 V	$V_{10} = 25 V_{10}$	25°C		0.6		pА
IВ	input bias current (see Note 4	·)	V _O = 2.5 V,	V _{IC} = 2.5 V	125°C		9	35	nA
\/	Common-mode input voltage	range			25°C	0 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	Ū			Full range	0 to 3.5			V
					25°C	3.2	3.9		
∨он	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	−55°C	3	3.9		V
					125°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	Lorgo oignal differential				25°C	25	170		
AVD	Large-signal differential voltage amplification		$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 100 \text{ k}\Omega$	−55°C	15	290		V/mV
	renage ampineation				125°C	15	120		
					25°C	65	91		
CMRR	Common-mode rejection ratio)	$V_{IC} = V_{ICR}min$		−55°C	60	89		dB
					125°C	60	91		
	Supply-voltage rejection ratio				25°C	70	93		
ksvr	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{DD} = 5 V \text{ to } 10 V,$	V _O = 1.4 V	−55°C	60	91		dB
					125°C	60	94		
			V _O = 2.5 V,	V _{IC} = 2.5 V,	25°C		420	1120	
IDD	Supply current (four amplifier	s)	No load	$v_{1C} = 2.5 v_{2}$	−55°C		680	1760	μΑ
					125°C		280	720	

[†] Full range is -55° C to 125° C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CO	NDITIONS	т _А †		.C27M4I .C27M9I		
						MIN	TYP	MAX	
		TLC27M4M	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		1.1	10	
V	Input offset voltage		R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
VIO	input onset voltage	TLC27M9M	V _O = 1.4 V,	V _{IC} = 0,	25°C		220	1200	μV
			R _S = 50 Ω,	RL = 100 kΩ	Full range			4300	μv
ανιο	Average temperature coeffi offset voltage	cient of input			25°C to 125°C		2.1		μV/°C
l.e.	Input offset current (see No	to (1)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.1		pА
10	input onset current (see No	le 4)	vO = 5 v,	vIC = 2 v	125°C		1.8	15	nA
lun.	Input biog ourrept (ago Not	. 4)	V _O = 5 V,	VIC = 5 V	25°C		0.7		pА
ΙB	Input bias current (see Note	; +)	v0 = 5 v,	v C = 2 v	125°C		10	35	nA
\ <i>\</i>	Common-mode input voltag	je range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	0 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	−55°C	7.8	8.6		V
					125°C	7.8	8.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	Large-signal differential				25°C	25	275		
AVD	voltage amplification		V _O = 1 V to 6 V,	$R_L = 100 \text{ k}\Omega$	−55°C	15	420		V/m∖
					125°C	15	190		
					25°C	65	94		
CMRR	Common-mode rejection ra	tio	$V_{IC} = V_{ICR}min$		−55°C	60	93		dB
					125°C	60	93		
	Supply-voltage rejection rat	io			25°C	70	93		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{DD} = 5 V \text{ to } 10 V,$	V _O = 1.4 V	−55°C	60	91		dB
					125°C	60	94		
			V _O = 5 V,	V _{IC} = 5 V,	25°C		570	1200	
IDD	Supply current (four amplifi	ers)	No load	чю — э v,	−55°C		980	2000	μA
					125°C		360	960	

[†] Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics, V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

	DADAMETED	TEST CON		TL	.C27M4	(UNIT
	PARAMETER	TEST CONI	DITIONS	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$V_{O} = 1.4 V,$ R _S = 50 Ω ,	V _{IC} = 0, R _L = 100 kΩ		1.1	10	mV
α _{VIO}	Temperature coefficient of input offset voltage	$T_A = 25^{\circ}C$ to $70^{\circ}C$			1.7		μV/°C
Iю	Input offset current (see Note 4)	V _O = 2.5 V,	V _{IC} = 2.5 V		0.1		pА
I _{IB}	Input bias current (see Note 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$		0.6		pА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 4	-0.3 to 4.2		V
∨он	High-level output voltage	V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	3.2	3.9		V
VOL	Low-level output voltage	V _{ID} = -100 mV,	$I_{OL} = 0$		0	50	mV
AVD	Large-signal differential voltage amplification	$V_{O} = 0.25 V \text{ to } 2 V,$	RL= 100 kΩ	25	170		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$		65	91		dB
k SVR	Supply-voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	V _{DD} = 5 V to 10 V,	V _O = 1.4 V	70	93		dB
IDD	Supply current (four amplifiers)	V _O = 2.5 V, No load	V _{IC} = 2.5 V,		420	1120	μΑ

electrical characteristics, V_{DD} = 10 V, T_A = 25°C (unless otherwise noted)

	DADAMETED	TEST CON	DITIONS	TL	.C27M4	ſ	LINUT
	PARAMETER	TEST CONI	JIIONS	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	V _O = 1.4 V, R _S = 50 Ω,	$V_{IC} = 0,$ R _L = 100 k Ω		1.1	10	mV
ανιο	Temperature coefficient of input offset voltage	$T_A = 25^{\circ}C$ to $70^{\circ}C$			2.1		μV/°C
IIO	Input offset current (see Note 4)	V _O = 5 V,	V _{IC} = 5 V		0.1		pА
I _{IB}	Input bias current (see Note 4)	V _O = 5 V,	$V_{IC} = 5 V$		0.7		pА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 9	-0.3 to 9.2		V
Vон	High-level output voltage	V _{ID} = 100 mV,	RL = 100 kΩ	8	8.7		V
VOL	Low-level output voltage	V _{ID} = -100 mV,	IOT = 0		0	50	mV
A _{VD}	Large-signal differential voltage amplification	V _O = 1 V to 6 V,	R _L = 100 kΩ	25	275		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$		65	94		dB
k SVR	Supply-voltage rejection ratio ($\Delta V_{DD} / \Delta V_{IO}$)	V _{DD} = 5 V to 10 V,	V _O = 1.4 V	70	93		dB
I _{DD}	Supply current (four amplifiers)	V _O = 5 V, No load	V _{IC} = 5 V,		570	1200	μΑ

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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	PARAMETER	TEST	CONDITIONS	TA		TLC27M4C TLC27M4AC TLC27M4BC TLC27M9C		
					MIN	TYP	MAX	
				25°C		0.43		
			VIPP = 1 V	0°C		0.46		
SR	Close rate at unity gain	$R_{L} = 100 \Omega,$		70°C		0.36		1////
SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
		<u>j</u>	VIPP = 2.5 V	5 V 0°C 0.43				
				70°C		0.34		1
Vn	Equivalent input noise voltage	f = 1 kHz _, See Figure 2	R _S = 20 Ω	25°C		32		nV/√Hz
				25°C		55		
Вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ $R_{I} = 100 \text{ k}\Omega,$	C _L = 20 pF, See Figure 1	0°C		60		kHz
		KL = 100 K22,	Gee rigure r	70°C		50		1
				25°C		525		
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	0°C		610		kHz
		Geen igure 5		70°C		400		1
				25°C		40°		
φm		$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		41°		1
		$O_{L} = 20 \text{ pr},$	See Figure 3	70°C	1	39°		1

operating characteristics at specified free-air temperature, V_{DD} = 5 V

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST CO	NDITIONS	TA	TL TL TL	.C27M4 .C27M4 .C27M4 .C27M4	AC BC C	UNIT													
			1	25°C	MIN	TYP 0.62	MAX														
				23 C																	
		$P_{\rm L} = 100.0$	VIPP = 1 V			0.67															
SR	Slew rate at unity gain	R _L = 100 Ω, C _L = 20 pF,		70°C		0.51		V/µs													
	Siew rate at unity gain	See Figure 1		25°C		0.56		v/µ3													
		V _{IPP} = 5.5 V	V _{IPP} = 5.5 V 0°C		0.61																
				70°C		0.46															
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz													
				25°C		35															
ВОМ	Maximum output-swing bandwidth							$V_{O} = V_{OH}$					$V_O = V_{OH},$ $R_L = 100 k\Omega,$			C _L = 20 pF, See Figure 1	0°C		40		kHz
		NL = 100 K32,	Occ riguie i	70°C		30															
				25°C		635															
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	0°C		710		kHz													
				70°C		510															
			<i>.</i>	25°C		43°															
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		44°															
		0L - 20 pr,		70°C		42°															



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operating characteristics at specified free-air temperature, V_{DD} = 5 V

	PARAMETER	TEST CO	NDITIONS	TA	TLC27M4I TLC27M4AI TLC27M4BI TLC27M9I			UNIT		
					MIN	TYP	MAX			
				25°C		0.43				
			VIPP = 1 V	−40°C		0.51				
SR	Slow rate at upity gain	ew rate at unity gain $\begin{array}{c} R_L = 100 \ \Omega, \\ C_L = 20 \ pF, \\ See \ Figure \ 1 \end{array} \bigvee_{IPP} = \ 2.5 \ V$		85°C		0.35		Mue		
SK	Siew fale at unity gain					25°C	0.40			V/µs
				-40°C	0.48			1		
				85°C		0.32		1		
Vn	Equivalent input noise voltage	f = 1 kHz _, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz		
				25°C		55				
Вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ $R_{I} = 100 \text{ k}\Omega,$	C _L = 20 pF, See Figure 1	-40°C		75		kHz		
		$ \mathbf{K} = 100 \text{ Ks2},$	See Figure 1	85°C		45		1		
				25°C		525				
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	-40°C		770		kHz		
		See Figure 5		85°C		370		1		
				25°C		40°				
φm	Phase margin	$V_{I} = 10 \text{ mV},$	$f = B_1$,	-40°C		43°		1		
		C _L = 20 pF,	See Figure 3	85°C		38°		1		

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST CO	TEST CONDITIONS			TLC27M4I TLC27M4AI TLC27M4BI TLC27M9I											
			-		MIN	TYP	MAX										
				25°C		0.62											
			V _{IPP} = 1 V	-40°C		0.77											
SR	Slow rate at upity gain	$R_L = 100 \Omega$		85°C		0.47		Muo									
SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/µs									
				V _{IPP} = 5.5 V	-40°C		0.70										
				85°C		0.44											
Vn	Equivalent input noise voltage	f = 1 kHz _, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz									
				25°C		35											
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$	$V_O = V_{OH}$	$V_O = V_{OH}$	$V_O = V_{OH}$	$V_O = V_{OH}$	$V_{O} = V_{OH}$	VO = VOH, R _L = 100 kΩ,	$V_O = V_{OH}$	$V_O = V_{OH}$	VO = VOH, $R_{L} = 100 kO$	C _L = 20 pF, See Figure 1	-40°C		45		kHz
		NL = 100 KS2,	Occ righter	85°C		25											
				25°C		635											
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	-40°C		880		kHz									
		See Figure 5		85°C		480											
				25°C		43°											
φm	m Phase margin $V_I = 10 \text{ m}$	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	= 10 mV, f = B ₁ , = 20 pF, See Figure 3			46°											
		ο _L – 20 ρι,		85°C		41°											



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	PARAMETER	TEST	CONDITIONS	TA		.C27M4 .C27M9		UNIT
					MIN	TYP	MAX	1
				25°C		0.43		
			V _{IPP} = 1 V	−55°C		0.54		
SR	Slew rate at unity gain	R _L = 100 Ω, C _L = 20 pF,		125°C		0.29		
SK	Siew rate at unity gain	See Figure 1		25°C		0.40		V/μs
			VIPP = 2.5 V	−55°C		0.50		
				125°C		0.28		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz
				25°C		55		
Вом	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_I = 100 \text{ k}\Omega,$	C _L = 20 pF, See Figure 1	−55°C		80		kHz
		INC - 100 KS2,	See rigule i	125°C		40		1
				25°C		525		
В ₁	Unity-gain bandwidth	VI = 10 mV, See Figure 3	C _L = 20 pF,	−55°C		850		kHz
		Georigaio S		125°C		330		
				25°C		40°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−55°C		44°		
		Ο _L = 20 pr,	See rigule 3	125°C		36°		1

operating characteristics at specified free-air temperature, V_{DD} = 5 V

operating characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V

	PARAMETER	TEST C	ONDITIONS	ТА	-	27M4N 27M9N		UNIT			
					MIN	TYP	MAX				
				25°C		0.62					
			V _{IPP} = 1 V	−55°C		0.81					
00		$R_L = 100 \Omega$		125°C		0.38		1////			
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs			
		gaio i	VIPP = 5.5 V	−55°C		0.73					
				125°C		0.35					
v _n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz			
				25°C		35					
Вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R _L = 100 k Ω ,	C _L = 20 pF, See Figure 1	−55°C		50		kHz			
		$K_{L} = 100 \text{ Ksz},$	See Figure 1	125°C		20					
				25°C		635					
B ₁	Unity-gain bandwidth	VI = 10 mV, See Figure 3	C _L = 20 pF,	−55°C		960		kHz			
		See Figure 5		125°C		440					
				25°C		43°					
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$				f = B ₁ , See Figure 3	−55°C		47°		
		$O_{L} = 20 \text{pr},$	See Figure S	125°C		39°					



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operating characteristics, $V_{DD} = 5 V$, $T_A = 25^{\circ}C$

	PARAMETER	TEST CO	NDITIONS	TL	C27M4	(UNIT
	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$R_{L} = 100 \text{ k}\Omega,$	V _{IPP} = 1 V		0.43		V/µs
5K	Siew rate at unity gain	C _L = 20 pF, See Figure 1	V _{IPP} = 2.5 V		0.40		v/µs
Vn	Equivalent input noise voltage	f = 1 kHz _, See Figure 2	R _S = 20 Ω,		32		nV/√Hz
вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R _L = 100 kΩ,	C _L = 20 pF, See Figure 1		55		kHz
В ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,		525		kHz
φm	Phase margin	V _I = 10 mV, C _L = 20 pF,	f = B ₁ , See Figure 3		40°		

operating characteristics, V_{DD} = 10 V, T_A = 25°C

	PARAMETER	TEST CO	IDITIONS	TL	C27M4)	(UNIT
	FARAMETER	1251 COI	NDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	R _L = 100 kΩ, C _L = 20 pF,	V _{IPP} = 1 V		0.62		V/µs
SK		See Figure 1	VIPP = 5.5 V		0.56		ν/μδ
V _n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,		32		nV/√Hz
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R _L = 100 kΩ,	C _L = 20 pF, See Figure 1		35		kHz
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,		635		kHz
φ _m	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3		43°		

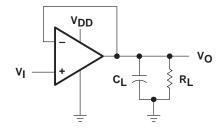


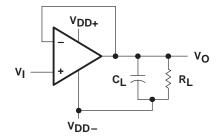
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PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC27M4 and TLC27M9 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

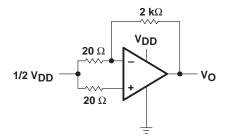




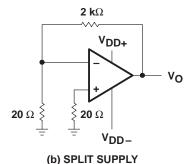
(a) SINGLE SUPPLY



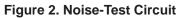


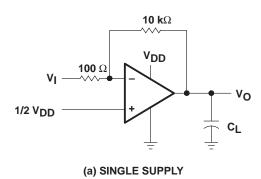












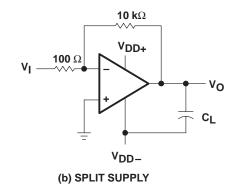


Figure 3. Gain-of-100 Inverting Amplifier



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PARAMETER MEASUREMENT INFORMATION

input bias current

Because of the high input impedance of the TLC27M4 and TLC27M9 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- 2. Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution—many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current; the voltage drop across the series resistor is measured and the bias current is calculated. This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

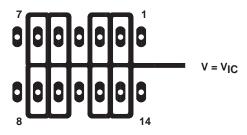


Figure 4. Isolation Metal Around Device Inputs (J and N packages)

low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the *Typical Characteristics* of this data sheet.



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PARAMETER MEASUREMENT INFORMATION

input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.

full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output, while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.



Figure 5. Full-Power-Response Output Signal

test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.



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TYPICAL CHARACTERISTICS

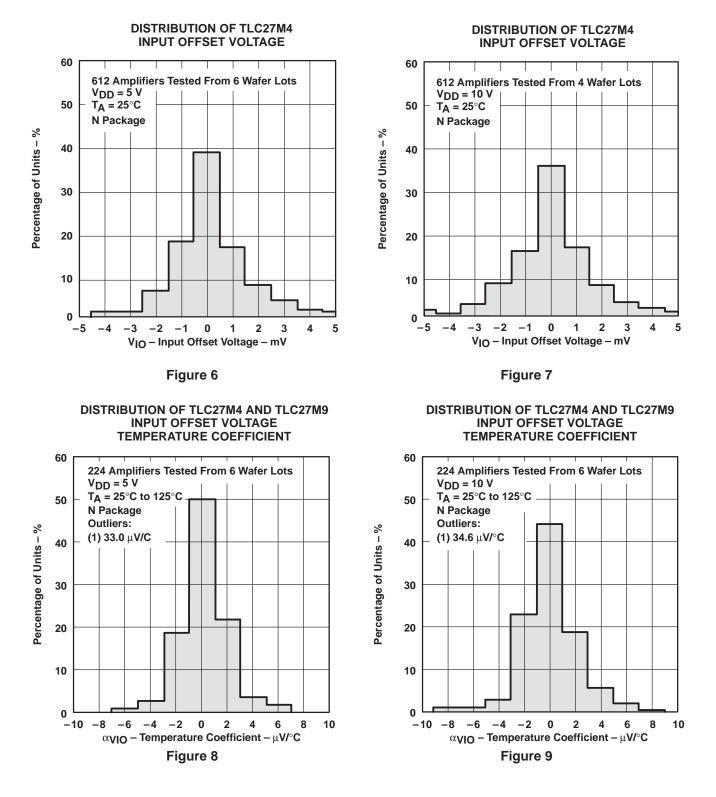
			FIGURE
VIO	Input offset voltage	Distribution	6, 7
αΛΙΟ	Temperature coefficient of input offset voltage	Distribution	8, 9
VOH	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V _{OL}	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I _{IB}	Input bias current	vs Free-air temperature	22
IIO	Input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
IDD	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	29
B ₁	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
	Phase shift	vs Frequency	32, 33
[¢] m	Phase margin	vs Supply voltage vs Free-air temperature vs Load capacitance	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37

Table of Graphs



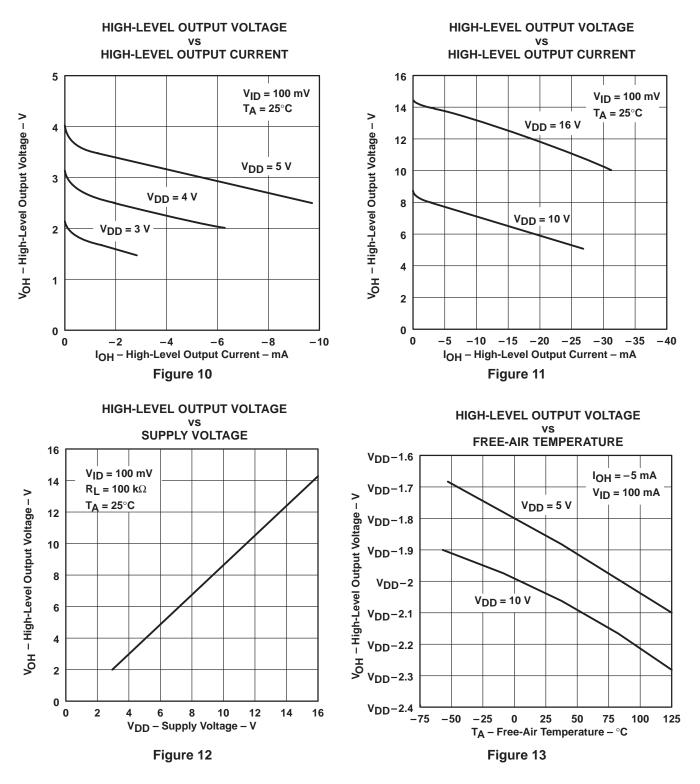
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TYPICAL CHARACTERISTICS





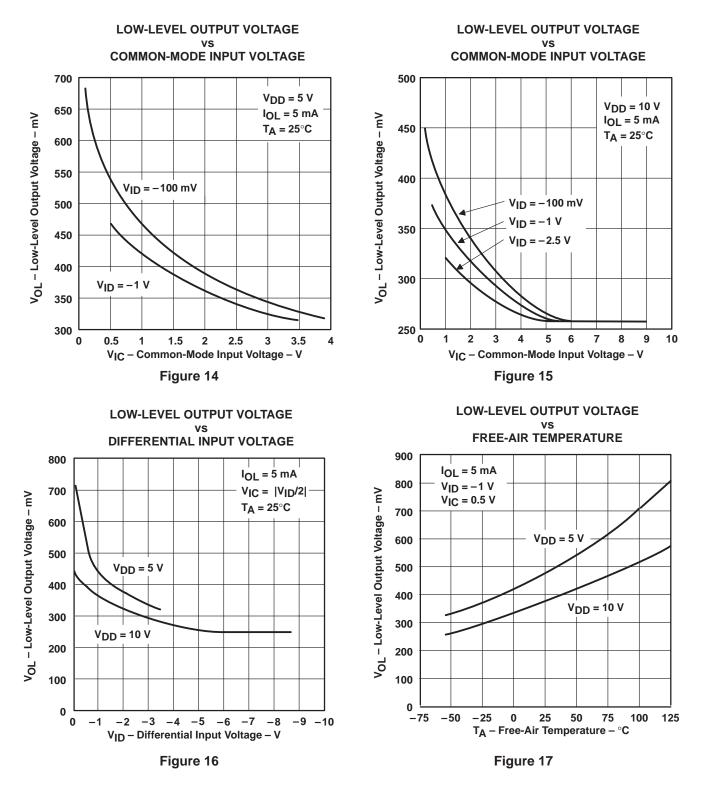
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TYPICAL CHARACTERISTICS[†]



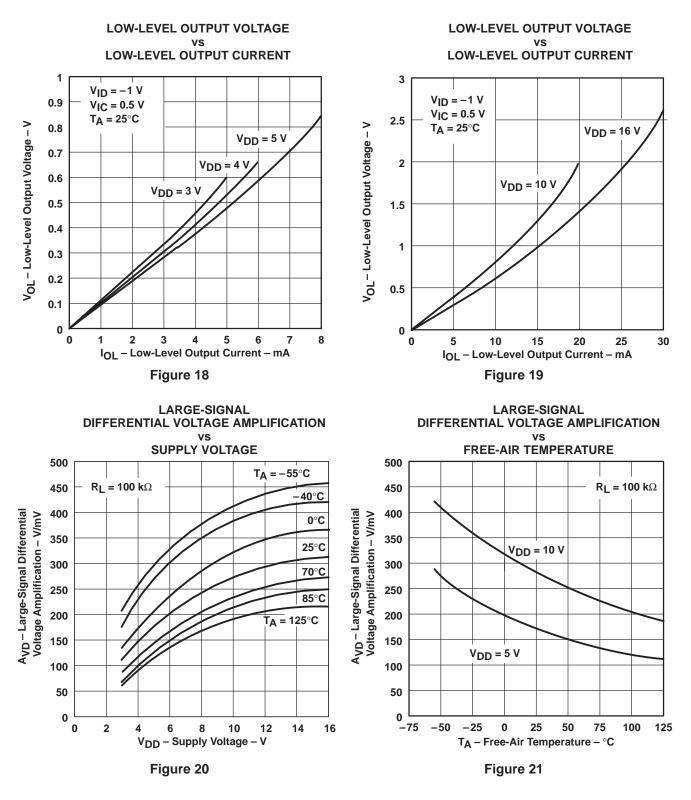
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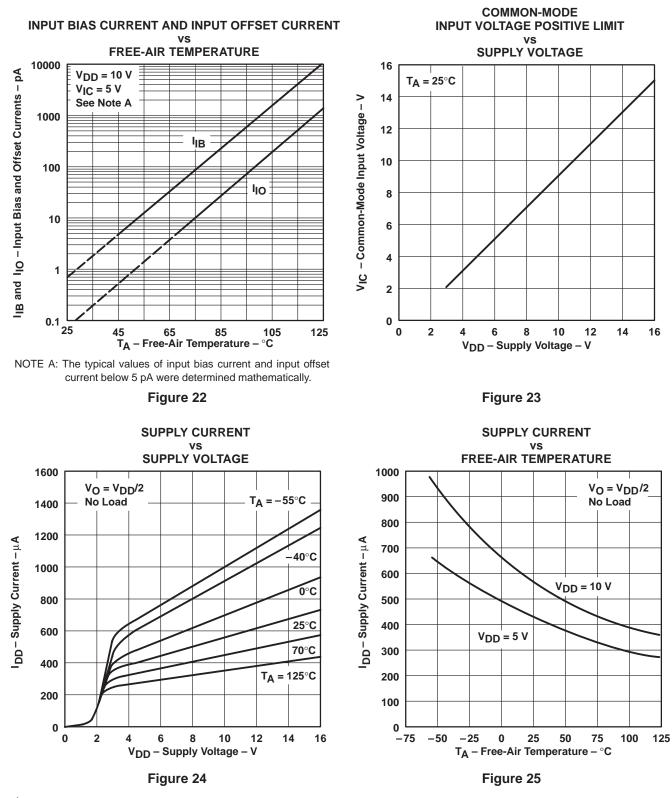
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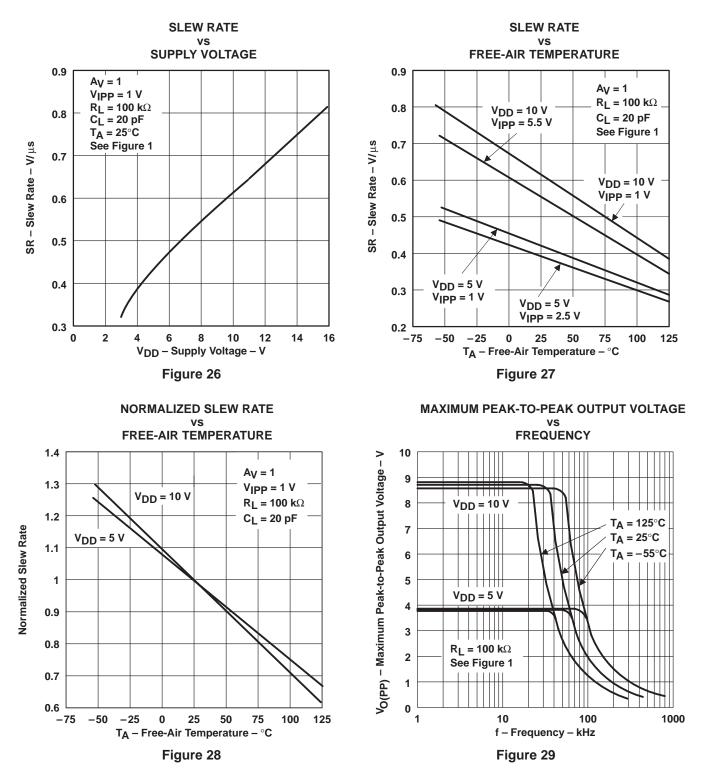
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TYPICAL CHARACTERISTICS[†]



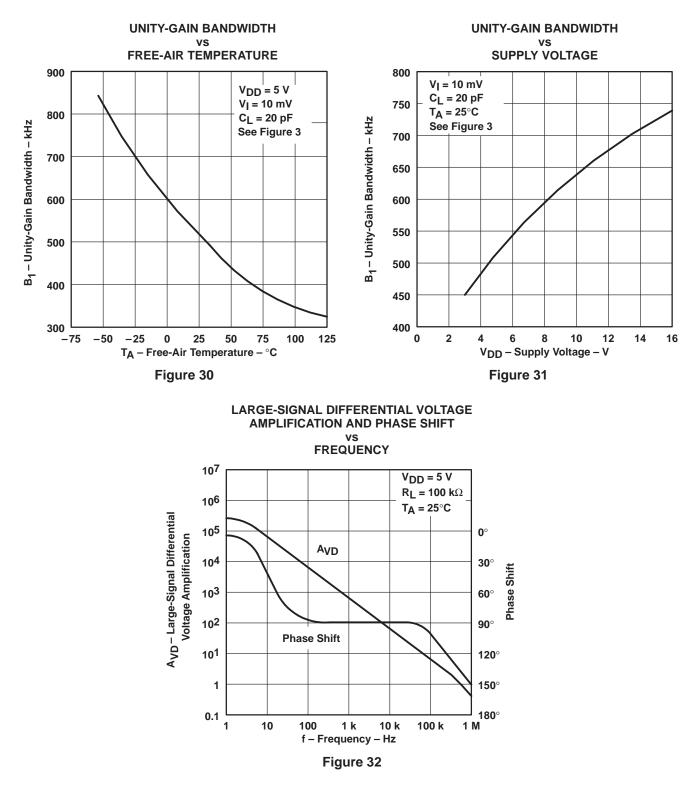
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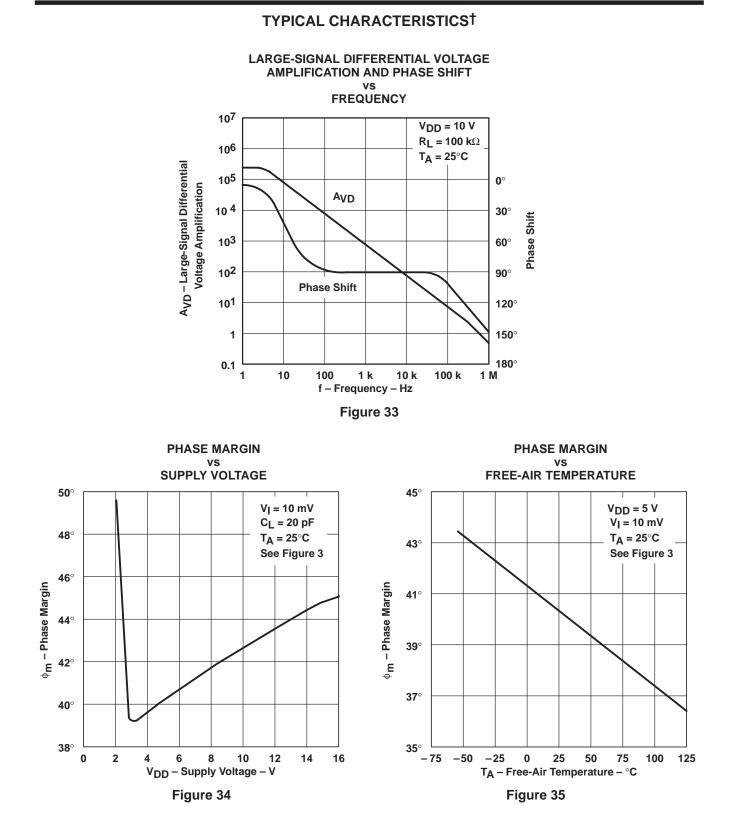
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TYPICAL CHARACTERISTICS[†]



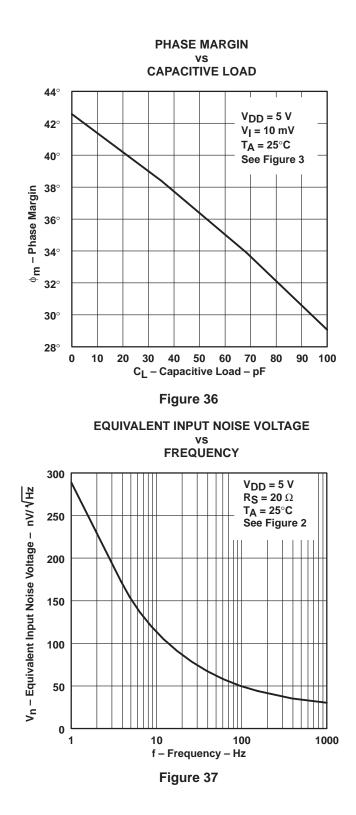
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TYPICAL CHARACTERISTICS





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APPLICATION INFORMATION

single-supply operation

While the TLC27M4 and TLC27M9 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27M4 and TLC27M9 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27M4 and TLC27M9 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- 1. Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

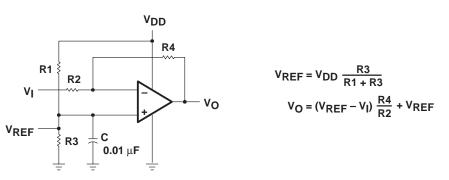
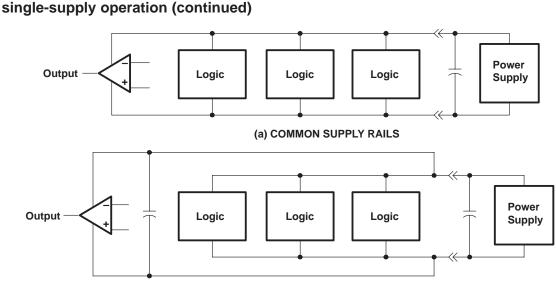


Figure 38. Inverting Amplifier With Voltage Reference



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APPLICATION INFORMATION



(b) SEPARATE BYPASSED SUPPLY RAILS (preferred)

Figure 39. Common Versus Separate Supply Rails

input characteristics

The TLC27M4 and TLC27M9 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at $V_{DD} - 1$ V at $T_A = 25^{\circ}$ C and at $V_{DD} - 1.5$ V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27M4 and TLC27M9 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1 μ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27M4 and TLC27M9 are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the *Parameter Measurement Information* section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

Unused amplifiers should be connected as unity-gain followers to avoid possible oscillation.

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27M4 and TLC27M9 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k Ω , since bipolar devices exhibit greater noise currents.



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APPLICATION INFORMATION



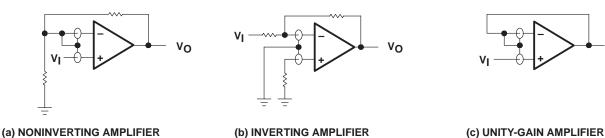
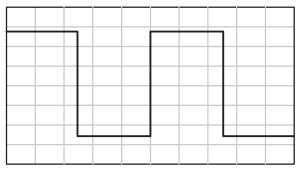


Figure 40. Guard-Ring Schemes

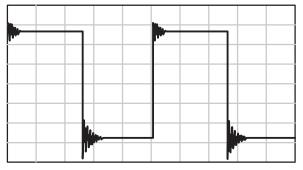
output characteristics

The output stage of the TLC27M4 and TLC27M9 is designed to sink and source relatively high amounts of current (see *typical characteristics*). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC27M4 and TLC27M9 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.

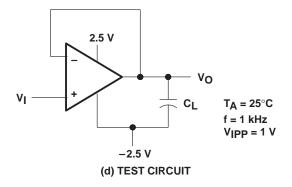


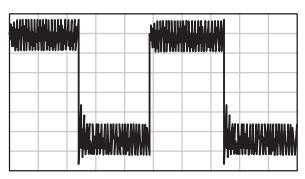
(a) $C_L = 20 \text{ pF}$, $R_L = \text{NO LOAD}$



۷o

(b) $C_L = 170 \text{ pF}$, $R_L = \text{NO LOAD}$





(c) $C_L = 190 \text{ pF}$, $R_L = \text{NO LOAD}$



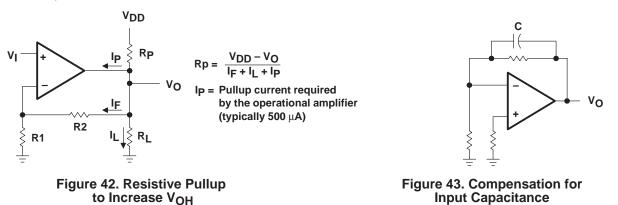


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APPLICATION INFORMATION

output characteristics (continued)

Although the TLC27M4 and TLC27M9 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R_P) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately 60 Ω and 180 Ω , depending on how hard the operational amplifier input is driven. With very low values of R_P , a voltage offset from 0 V at the output occurs. Second, pullup resistor R_P acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.



feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

electrostatic discharge protection

The TLC27M4 and TLC27M9 incorporate an internal electrostatic discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices, as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature-dependent and have the characteristics of a reverse-biased diode.

latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27M4 and TLC27M9 inputs and outputs were designed to withstand –100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

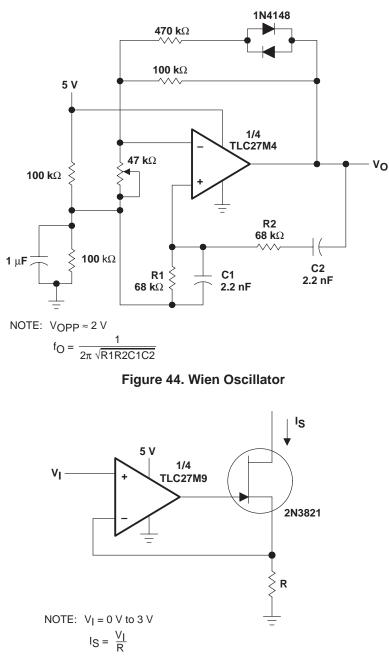


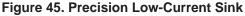
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APPLICATION INFORMATION

latch-up (continued)

The current path established if latch-up occurs is usually between the positive supply rail and ground; it can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

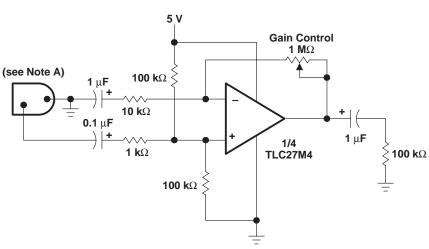


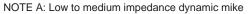




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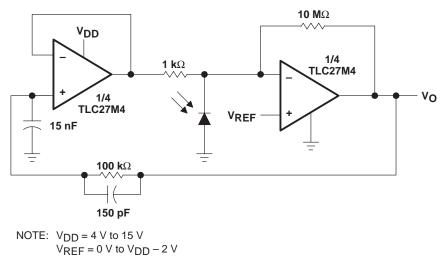
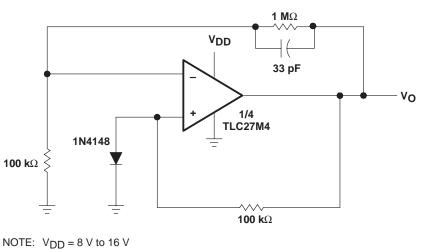


Figure 47. Photo-Diode Amplifier With Ambient Light Rejection



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APPLICATION INFORMATION

1E: $V_{DD} = 8 V \text{ to } 16 V V_{O} = 5 V, 10 \text{ mA}$



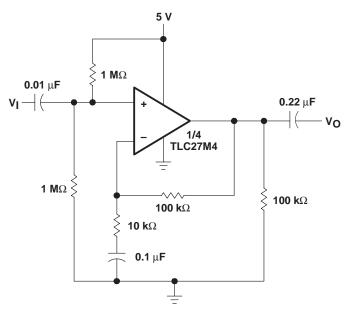


Figure 49. Single-Rail AC Amplifier



8-Dec-2008

PACKAGING INFORMATION

TEXAS INSTRUMENTS www.ti.com

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	n MSL Peak Temp ⁽³⁾
5962-90604042A	OBSOLETE	LCCC	FK	20	-	TBD	Call TI	Call TI
TLC27M4ACD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4ACDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4ACDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4ACDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4ACN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4ACNE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4AID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4AIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4AIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4AIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4AIN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4AINE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4BCD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BCDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BCDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BCDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BCN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4BCNE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4BID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4BIN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4BINE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

PACKAGE OPTION ADDENDUM

WTEXAS INSTRUMENTS www.ti.com

8-Dec-2008

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³
TLC27M4CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M4CN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4CNE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4CNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4CPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI
TLC27M4CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4CPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4INE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M4IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4IPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M4MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLC27M4MJ	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI
TLC27M4MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI
TLC27M9CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIN
TLC27M9CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS &	CU NIPDAU	Level-1-260C-UNLIN

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
						no Sb/Br)		
TLC27M9CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M9CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M9CN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M9CNE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M9CNSLE	OBSOLETE	SO	NS	14		TBD	Call TI	Call TI
TLC27M9ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M9IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M9IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M9IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M9IN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M9INE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M9MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLC27M9MJ	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI
TLC27M9MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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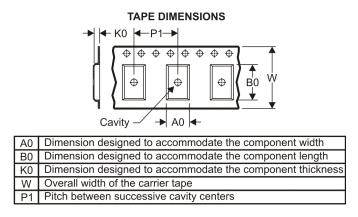


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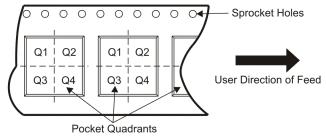
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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

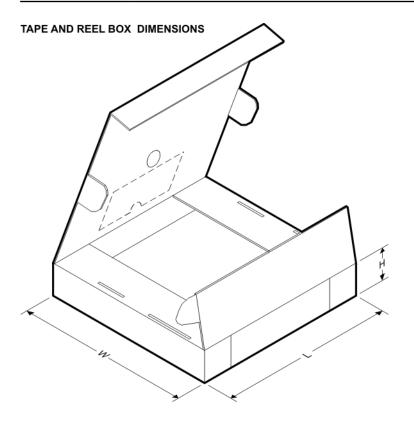


*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC27M4ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M4AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M4BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M4BIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M4CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M4CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC27M4CPWR	TSSOP	PW	14	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1
TLC27M4IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M4IPWR	TSSOP	PW	14	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1
TLC27M9CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27M9IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



PACKAGE MATERIALS INFORMATION

5-Aug-2008



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC27M4ACDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M4AIDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M4BCDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M4BIDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M4CDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M4CNSR	SO	NS	14	2000	346.0	346.0	33.0
TLC27M4CPWR	TSSOP	PW	14	2000	346.0	346.0	29.0
TLC27M4IDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M4IPWR	TSSOP	PW	14	2000	346.0	346.0	29.0
TLC27M9CDR	SOIC	D	14	2500	346.0	346.0	33.0
TLC27M9IDR	SOIC	D	14	2500	346.0	346.0	33.0

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